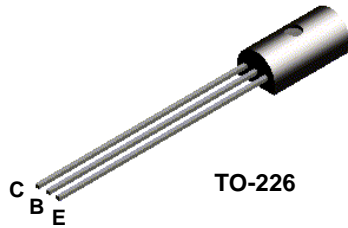


TN4033A



PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at currents to 500 mA and collector voltages up to 70V. Sourced from Process 67.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN4033A	
P _D	Total Device Dissipation Derate above 25°C	1.0	W
		8.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	50	°C/W

PNP General Purpose Amplifier

(continued)

TN4033A

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	80		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	80		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 60 \text{ V}, I_E = 0$ $V_{CB} = 60 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		50	nA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 100 \text{ } \mu\text{A}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}, T_A = -55^\circ\text{C}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}$	75 40 100 70 25	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.15 0.5	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.9	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 500 \text{ mA}, V_{CE} = 0.5 \text{ V}$		1.1	V

SMALL SIGNAL CHARACTERISTICS

C_{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		20	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0, f = 1.0 \text{ MHz}$		110	pF
h_{fe}	Small-Signal Current Gain	$I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	1.0	4.0	

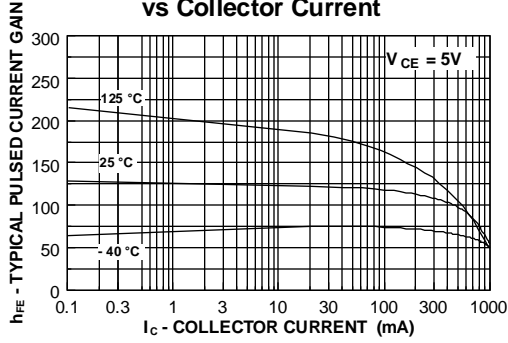
SWITCHING CHARACTERISTICS

t_s	Storage Time	$I_C = 500 \text{ mA}, I_{B1} = I_{B2} = 50 \text{ mA}$		350	ns
t_{on}	Turn-On Time	$I_C = 500 \text{ mA}, I_{B1} = 50 \text{ mA}$		100	ns
t_f	Fall Time	$I_C = 500 \text{ mA}, I_{B1} = I_{B2} = 50 \text{ mA}$		50	ns

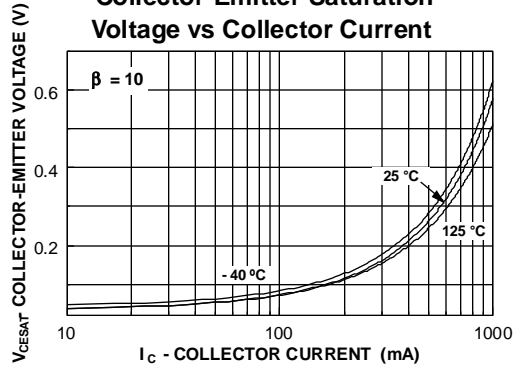
*Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 1.0\%$

Typical Characteristics

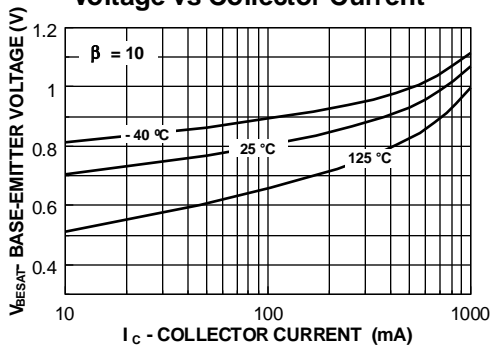
Typical Pulsed Current Gain vs Collector Current



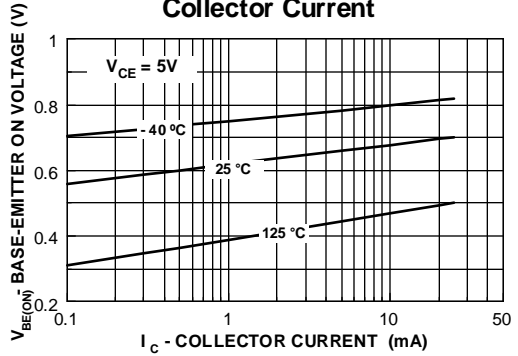
Collector-Emitter Saturation Voltage vs Collector Current



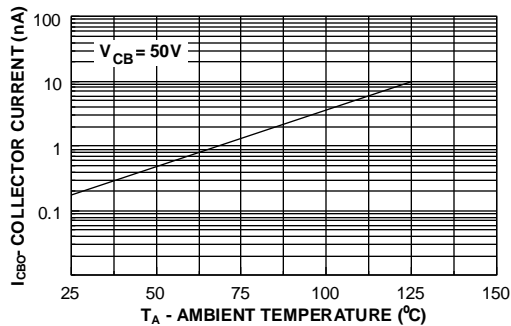
Base-Emitter Saturation Voltage vs Collector Current



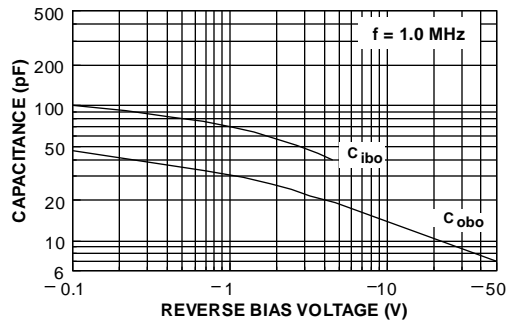
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

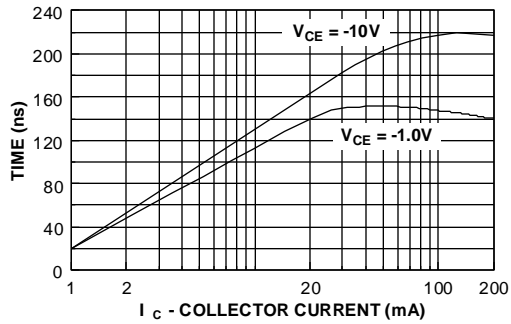


Collector-Base and Emitter-Base Capacitance vs Reverse Bias Voltage

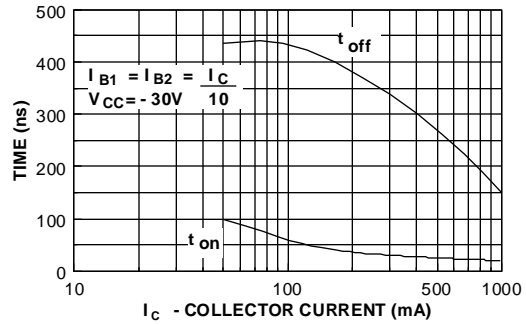


Typical Characteristics (continued)

Switching Times vs
Collector Current



Turn On and Turn Off Times vs
Collector Current



Power Dissipation vs
Ambient Temperature

